

**What Is Claimed Is:**

1           1.     A method of stabilizing parasitic capacitance in an  
2 LCD device, comprising the steps of:  
3           providing a substrate;  
4           forming a plurality of transversely expanding gate lines  
5                 on the substrate;  
6           forming a first insulating layer on the substrate and the  
7                 gate lines;  
8           performing a photolithography procedure using a photomask  
9                 to form a plurality of longitudinally expanding data  
10           lines and a plurality of metallic light shield  
11           layers on part of the first insulating layer,  
12           wherein the metallic light shield layers are located  
13           on both sides of the data line;  
14           forming a second insulating layer on the metallic light  
15                 shield layers and the data lines; and  
16           forming transparent conductive layers on part of the  
17                 second insulating layer.

1           2.     The method according to claim 1, further comprising  
2 the step of:  
3           forming conductive plugs penetrating the second  
4                 insulating layer to electrically connect the  
5           metallic light shield layers and the transparent  
6                 conductive layers.

1           3.     The method according to claim 1, wherein the  
2 substrate is a glass substrate.

1           4.     The method according to claim 1, wherein the first  
2     insulating layer is a silicon oxide ( $\text{SiO}_x$ ) layer.

1           5.     The method according to claim 1, wherein the second  
2     insulating layer is a silicon oxide ( $\text{SiO}_x$ ) layer.

1           6.     The method according to claim 1, wherein the metallic  
2     light shield layers and the data lines comprise Al and/or Mo.

1           7.     The method according to claim 1, wherein the  
2     transparent conductive layers are ITO (indium tin oxide) or IZO  
3     (indium zinc oxide) layers.

1           8.     The method according to claim 2, wherein the metallic  
2     light shield layers and the transparent conductive layers are  
3     equipotential.

1           9.     A method of stabilizing parasitic capacitance in an  
2     LCD device, comprising the steps of:

3           providing a glass substrate;

4           forming a plurality of transversely expanding gate lines  
5           on the glass substrate;

6           forming a first silicon oxide ( $\text{SiO}_x$ ) layer on the glass  
7           substrate and the gate lines;

8           performing a photolithography procedure using a photomask  
9           to form a plurality of longitudinally expanding data

10          lines and a plurality of metallic light shield  
11          layers on part of the first silicon oxide layer,  
12          wherein the metallic light shield layers are located  
13          on both sides of the data line;

14          forming a second silicon oxide ( $\text{SiO}_x$ ) layer on the  
15          metallic light shield layers and the data lines;

16 forming conductive plugs penetrating the second silicon  
17 oxide layer; and  
18 forming transparent conductive layers on part of the  
19 second silicon oxide layer, wherein the metallic  
20 light shield layers electrically connect the  
21 transparent conductive layers by means of the  
22 conductive plugs.

1 10. The method according to claim 9, wherein the metallic  
2 light shield layers and the data lines are equipotential.

1 11. The method according to claim 9, wherein the metallic  
2 light shield layers and the data lines comprise Al and/or Mo.

1 12. The method according to claim 9, wherein the  
2 transparent conductive layers are ITO (indium tin oxide) or IZO  
3 (indium zinc oxide) layers.